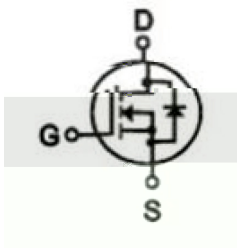
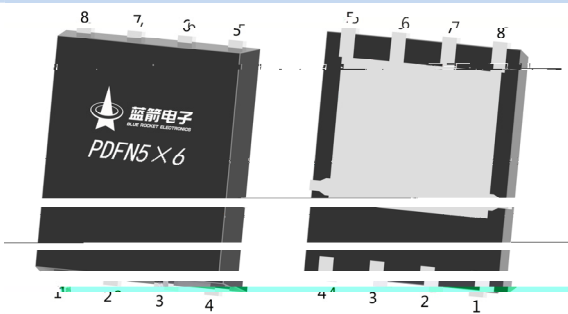


PDFN5×6 5 N 3 1
N-Channel MOSFET in a PDFN5×6 Plastic Package .

High Efficiency, Low $R_{DS(ON)}$ to minimize conductive loss; low Gate Charge for fast switching; Low Thermal resistance;
Qualified to AEC-Q101 Standards for High Reliability; HF Product.

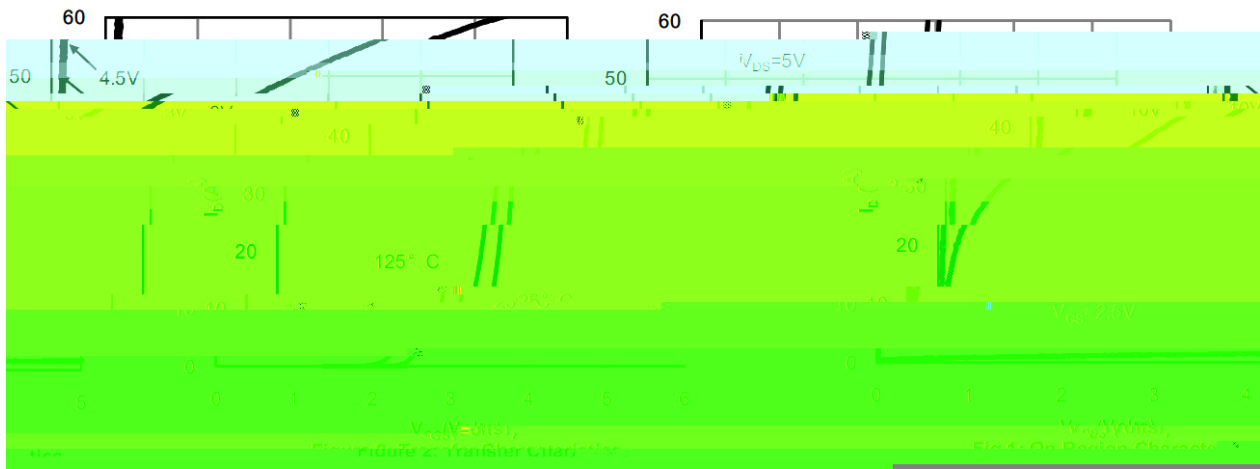
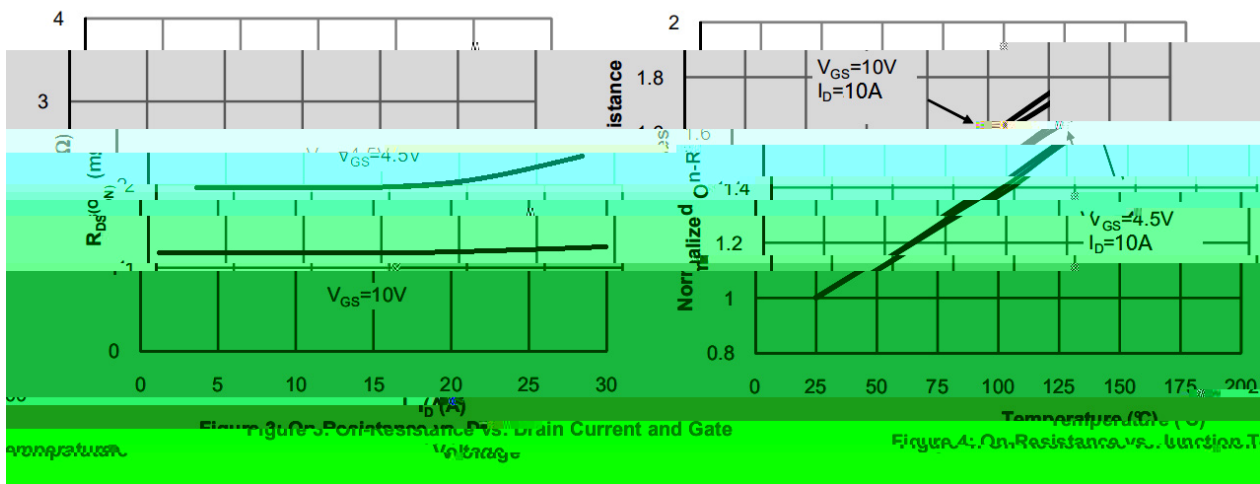
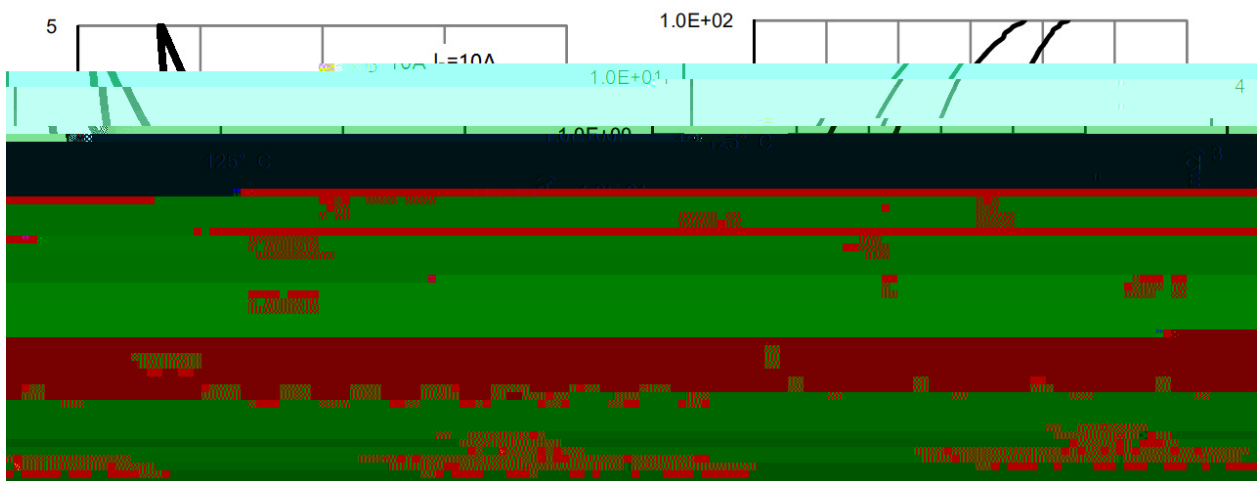
Battery Management, Meet the stringent requirements of automotive applications.

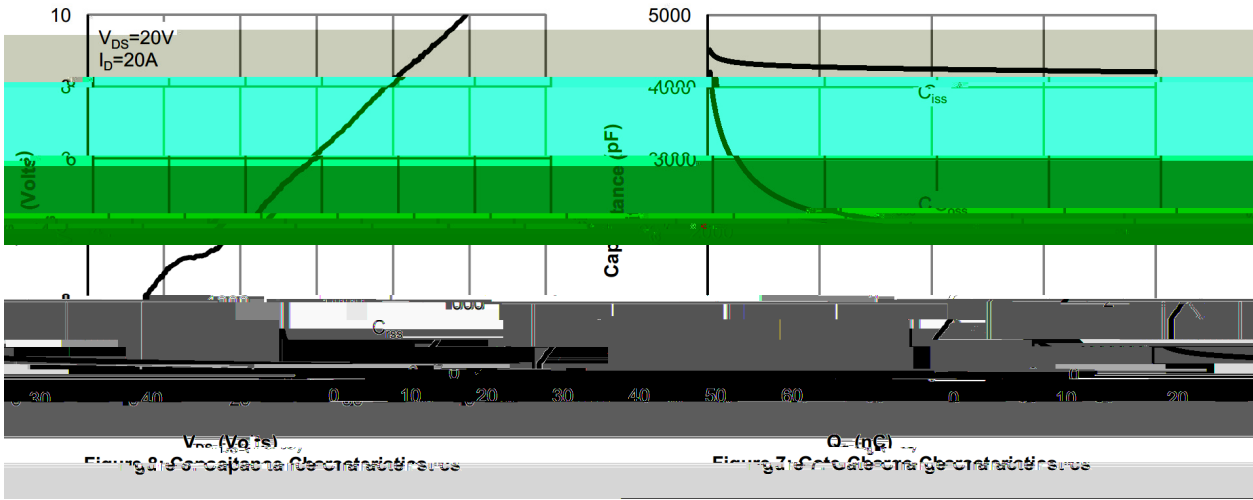
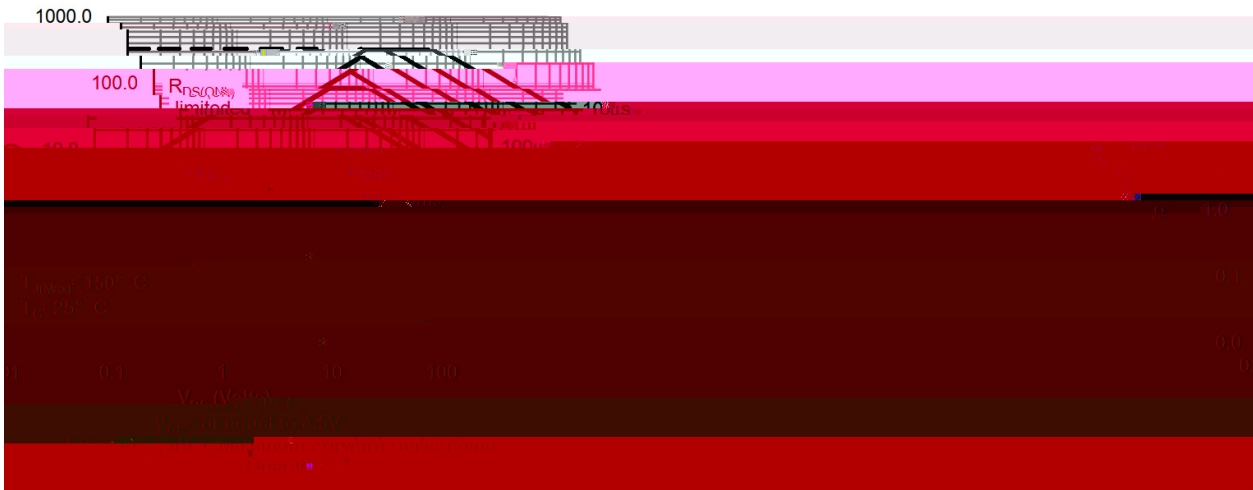
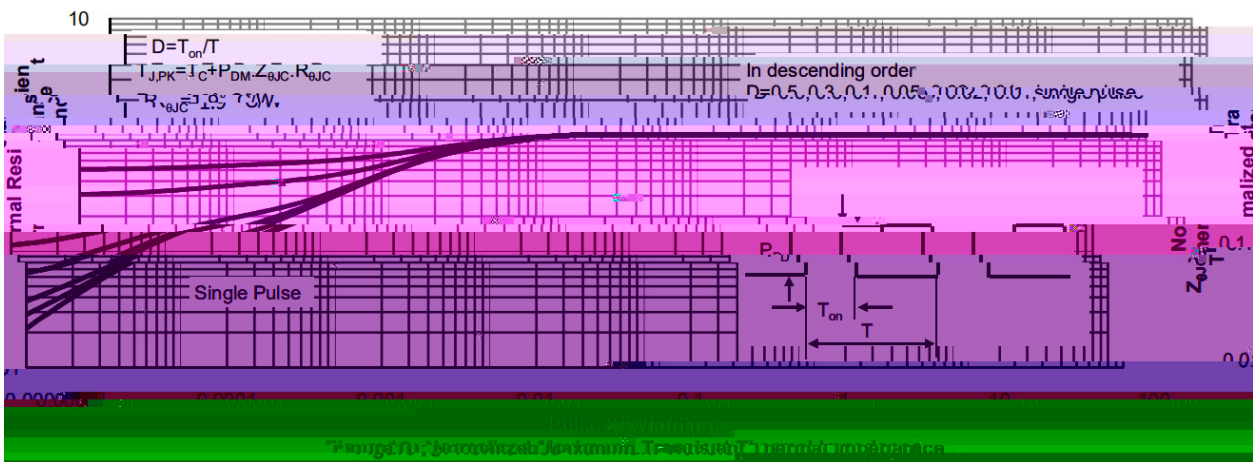


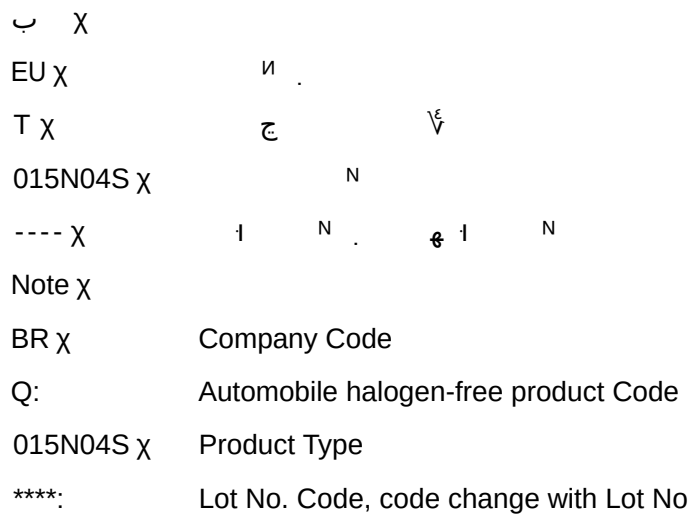
PIN1 2 3 S PIN4 G PIN5 6 7 8 D

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Drain Current - Continuous	I_D	170	A
Drain Current – Pulsed	I_{DM}	340	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	65	W
Single Pulse Avalanche Energy(L=0.5mH)	E_{AS}	358	mJ
Avalanche Current(L=0.5mH)	I_{AS}	32	A
Junction and Storage Temperature Range	T_j, T_{stg}	-55 to 150	
Thermal resistance, junction - case	$R_{\theta JC}$	1.9	/ W
Thermal resistance, junction - ambient	$R_{\theta JAGS}$		







- ب

χ
- 1

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□

150

200

ج

60

120sec;

1.Preheating:150~200 , Time:60~120sec.
- 2

□

255±5

ج

أ

5±0.5sec;

2.Peak Temp.:255±5 , Duration:5±0.5sec.
- 3

٧

د

2

10

/sec.

3. Cooling Speed: 2~10 /sec.

Note:

□ χ 260±5

ج χ 10±